

IN THE CLAIMS

Claims 1-15 (Canceled).

16 (Currently Amended). A device comprising:

a semiconductor substrate having at least one layer with conductive metal lines thereon; and

a dielectric material between the metal lines, said dielectric material having a surface abutting a conductive metal line, the conductive metal line having a smoother sidewall than the facing dielectric surface, said dielectric material is at least 50% porous.

Claim 17 (Canceled).

18 (Original). The device of claim 16 wherein the dielectric material is over a conductive layer.

19 (Original). The device of claim 16 wherein the dielectric material comprises a carbon-doped oxide.

20 (Original). The device of claim 16 wherein the dielectric material has a dielectric constant below about 3.0.

21 (Original). The device of claim 16 wherein the dielectric material comprises fluorinated silica glass.

22 (Original). The device of claim 16 wherein the dielectric material is a silsesquioxane-based material.

23 (Original). The device of claim 16 wherein the dielectric material has a thermal stability greater than about 400 degrees C.

24 (New). A device comprising:
a semiconductor substrate having at least one layer with conductive metal lines thereon; and
a porous carbon doped oxide between the metal lines, said porous carbon doped oxide having a surface abutting a conductive metal line, the conductive metal line having a smoother sidewall than the facing dielectric surface.

25 (New). The device of claim 24 wherein the carbon doped oxide is at least 50% porous.

26 (New). The device of claim 24 wherein said conductive doped oxide is over a conductive layer.

27 (New). The device of claim 25 wherein said carbon doped oxide has a dielectric constant below about 3.0.